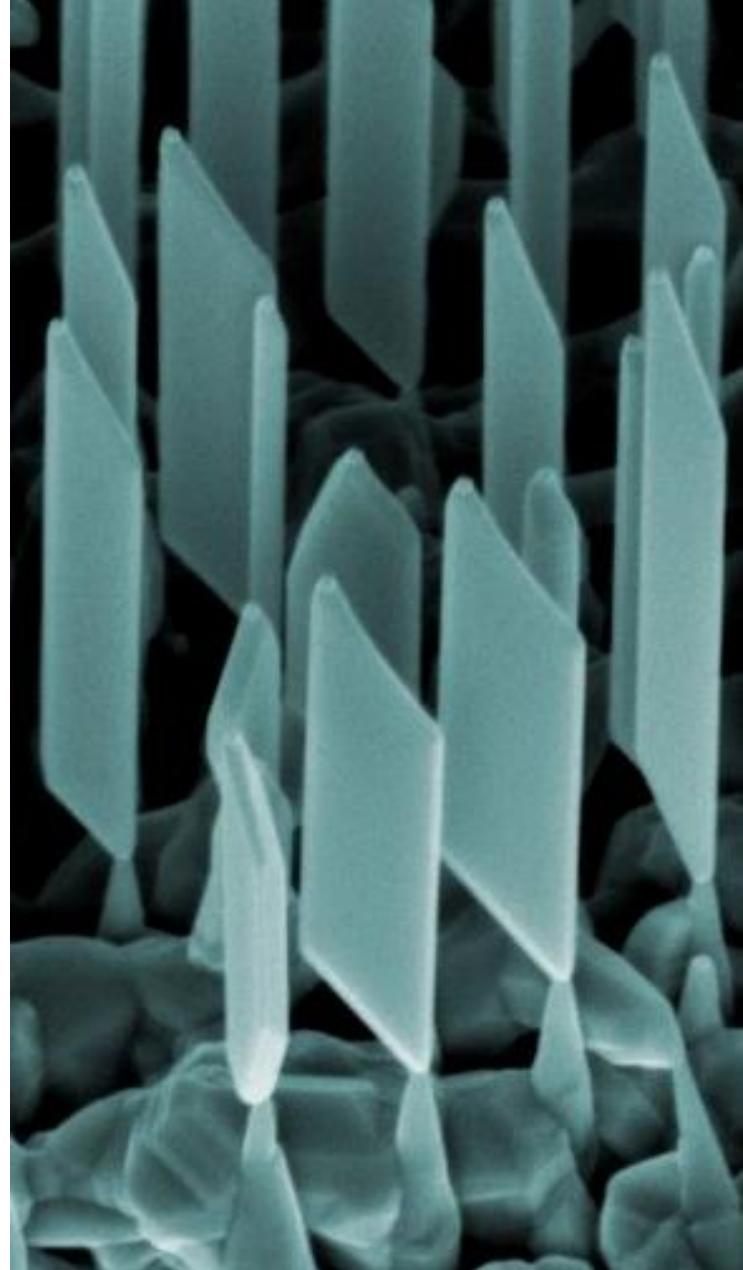




Hybrid superconductor-semiconductor Josephson junctions for quantum technologies

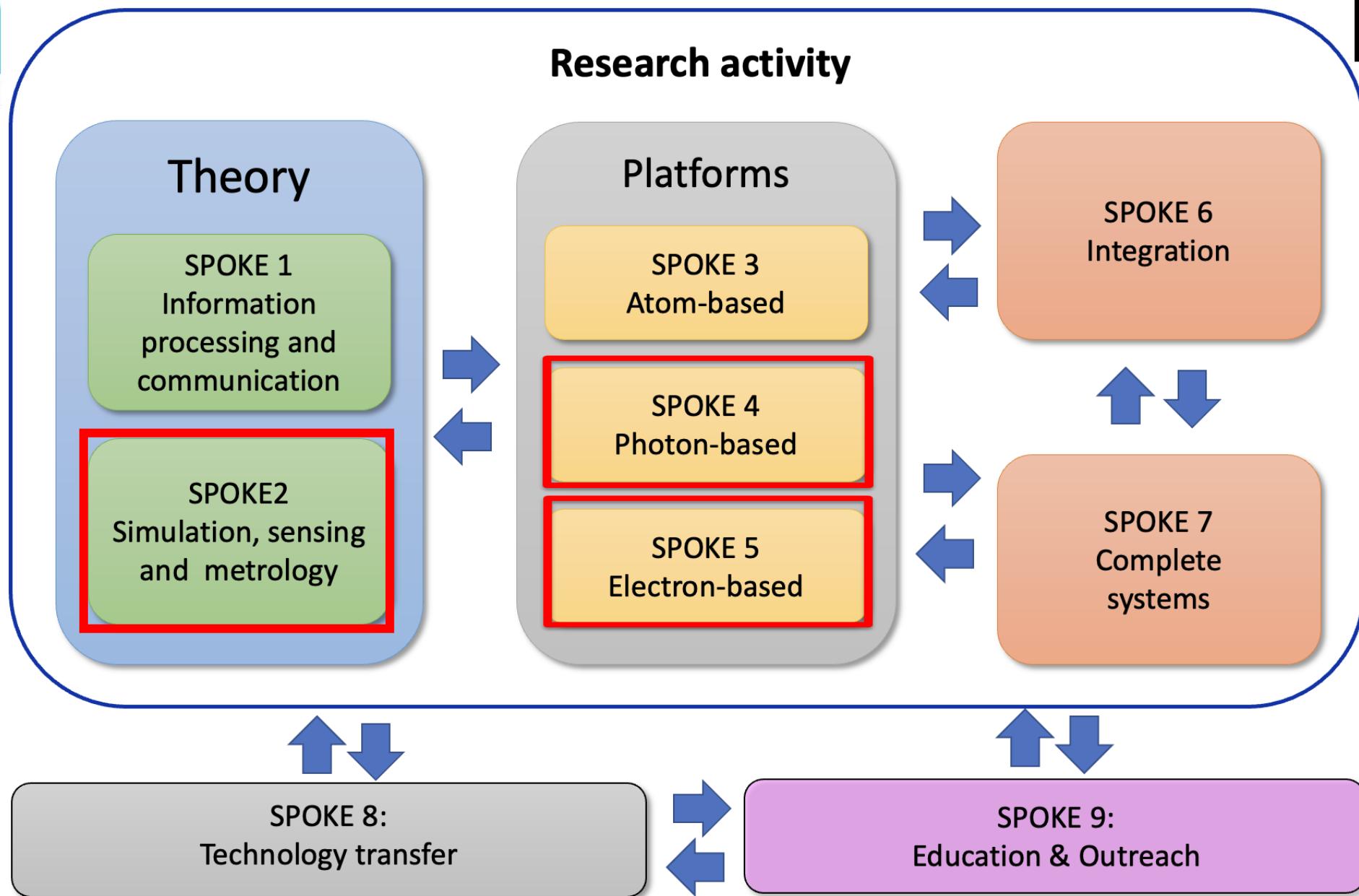
Stefan Heun

NEST, Istituto Nanoscienze-CNR and Scuola Normale Superiore, Pisa, Italy



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Activities Spoke 5

A5.1	Tunable emerging electronic configurations in hybrid/topological systems
A5.2	Novel nanomaterials for hybrid architectures
A5.3	Phase-sensitive architectures (SQUIPTs)
A5.4	Quantum energy management
A5.5	Tailored defects and molecules for QT
A5.6	Quantum interfacing, control and readout
A5.7	Innovative characterization techniques to probe quantum nature and performance (Ultra-fast and quantum-enhanced TEM of collective exitation)

InSb Nanoflag-based JJs

Growth activity



Isha Verma



Daniele
Ercolani



Valentina
Zannier



Lucia Sorba

Devices



Sedighe Salimian



Matteo Carrega
(CNR-SPIN)



Luca Chirolli

Transport



Bianca Turini



Andrea Iorio



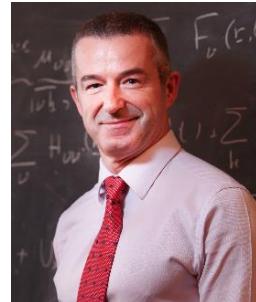
Alessandro
Crippa



Elia Strambini



Francesco
Giazotto



Fabio Beltram

Why InSb?

Small bandgap $E_g = 0.23 \text{ eV}$

Low effective mass $m/m_o = 0.018$

Strong SOC $E_{\text{SOC}} \sim 200 \mu\text{eV}$

Why InSb?

Small bandgap

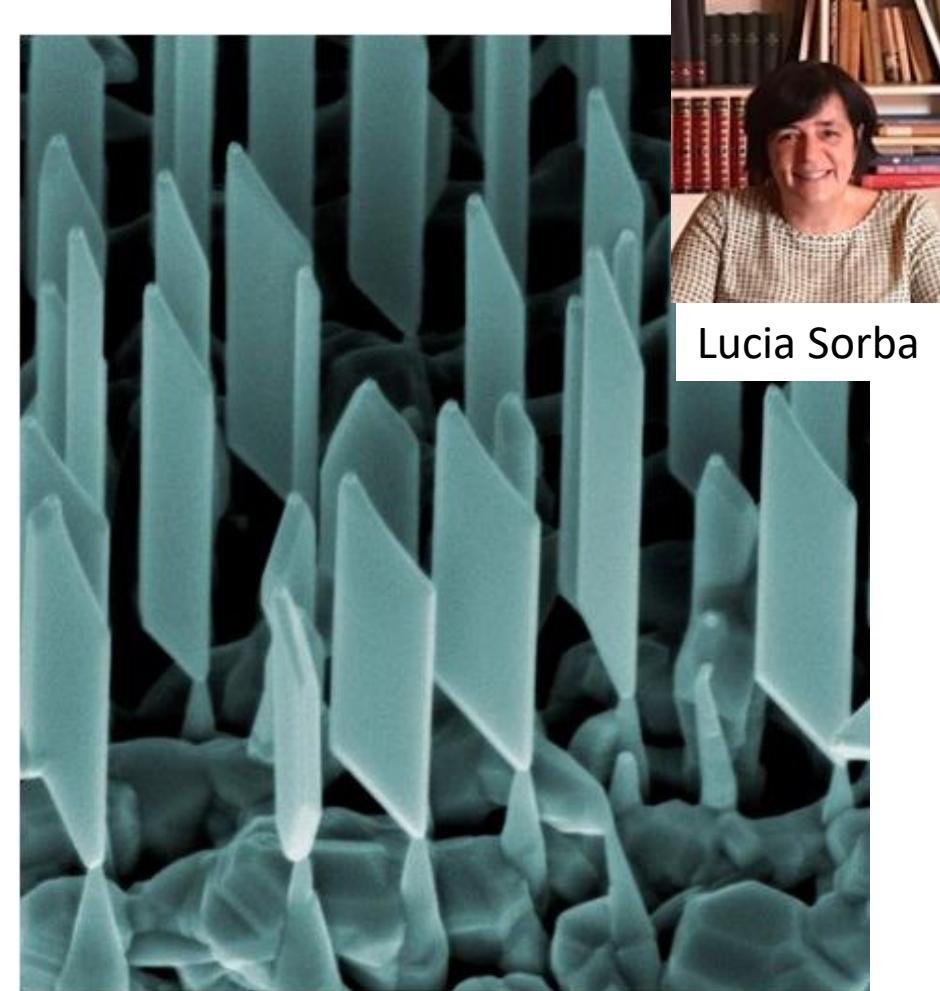
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Strong SOC

$$E_{\text{SOC}} \sim 200 \mu\text{eV}$$

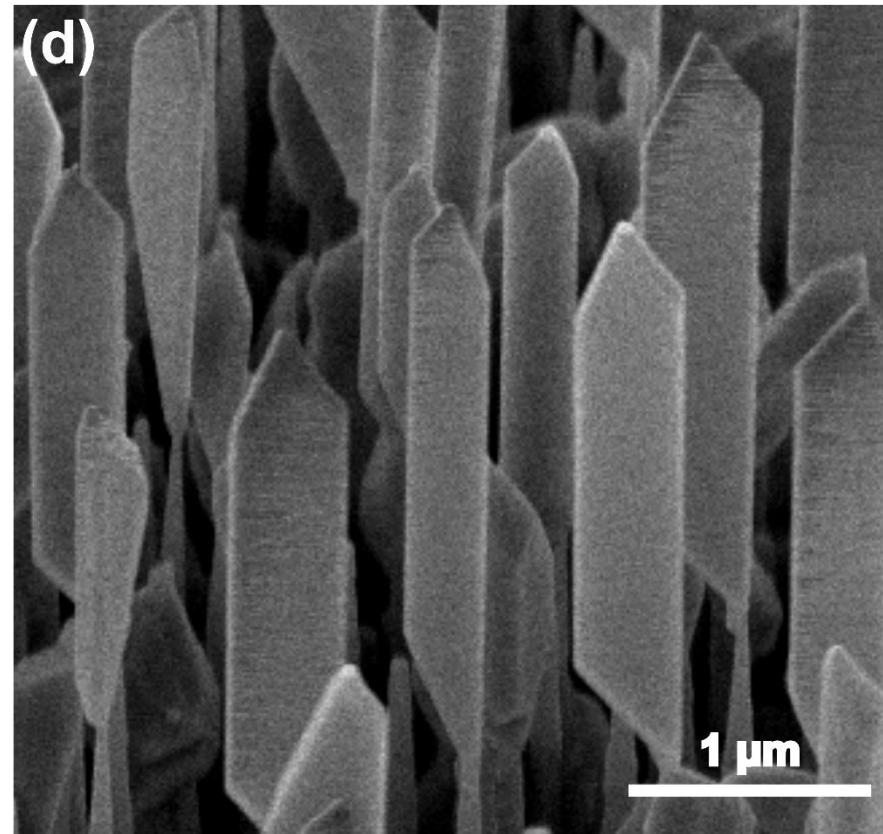
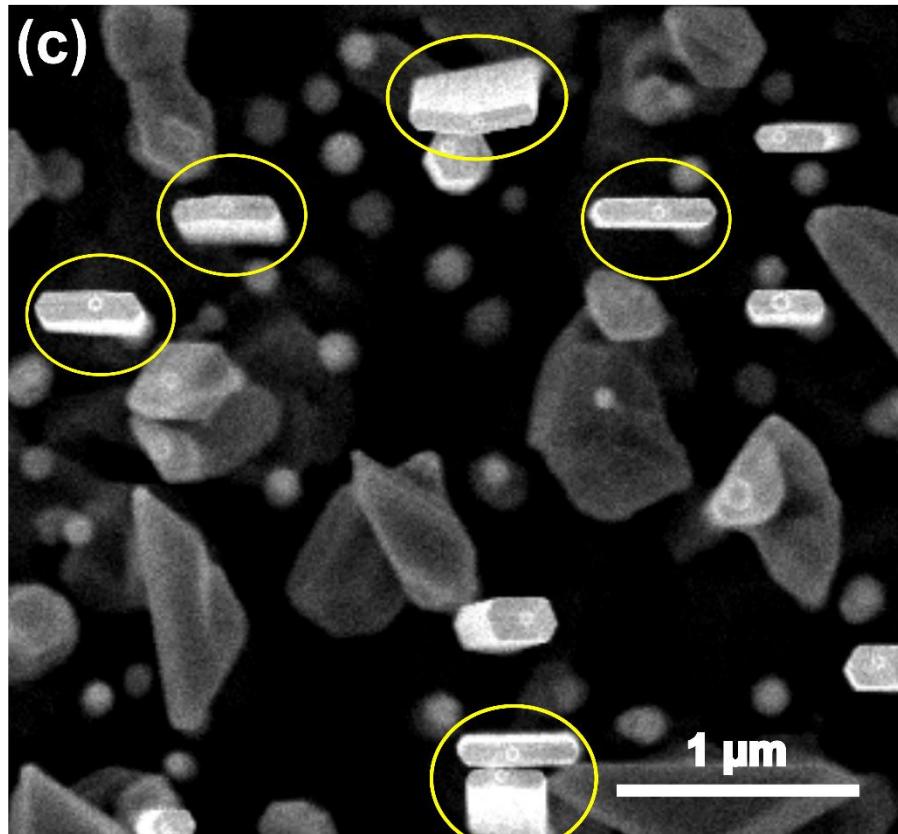
High-mobility 2D nanostructures



Growth of InSb nanoflags by CBE



Isha Verma

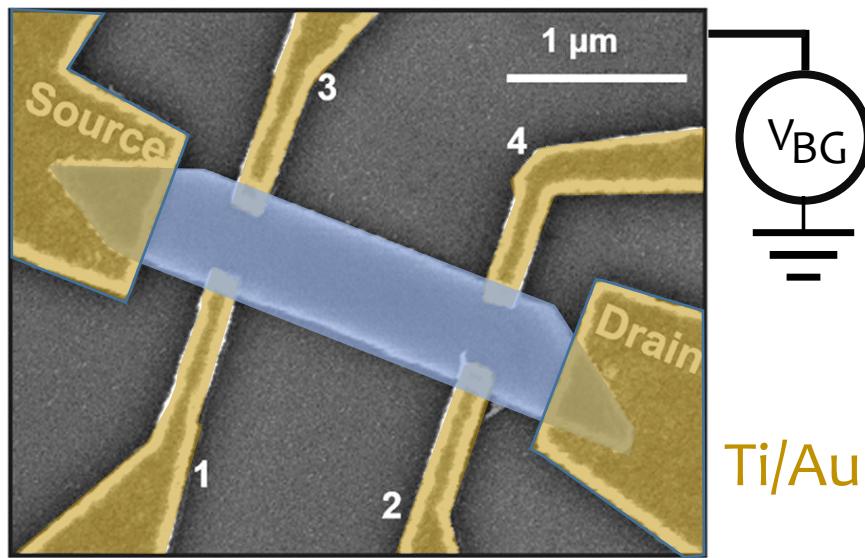


Defect-free InSb
zinc blende
lattice

InSb nanoflags:
Length 2-3 μ m
Width 500 nm
Thickness 100 nm

NFs show high mobility and giant g*-factor

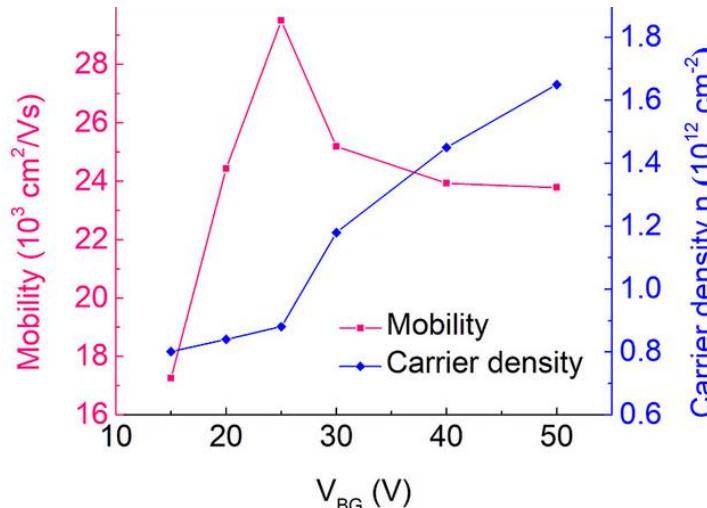
@ T = 4.2 K



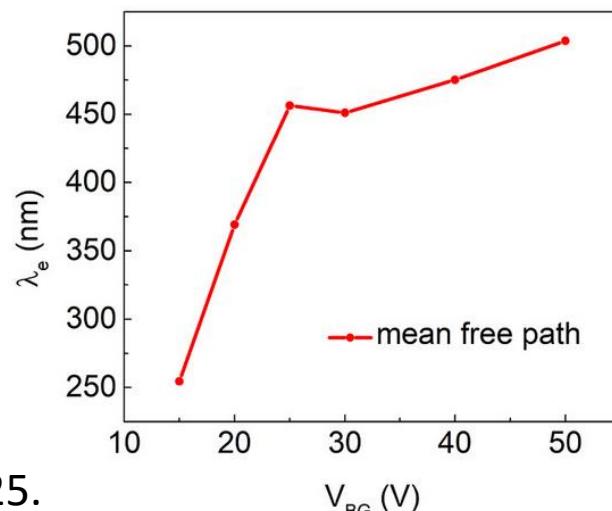
Ti/Au

@ T = 250 mK

$$g^* \sim 44$$

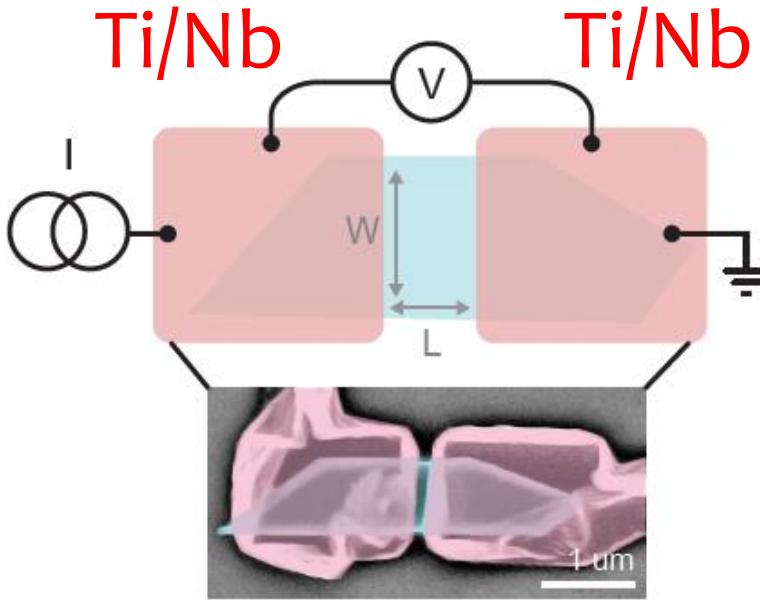


$$\mu_e \sim 29500 \text{ cm}^2/\text{Vs}$$



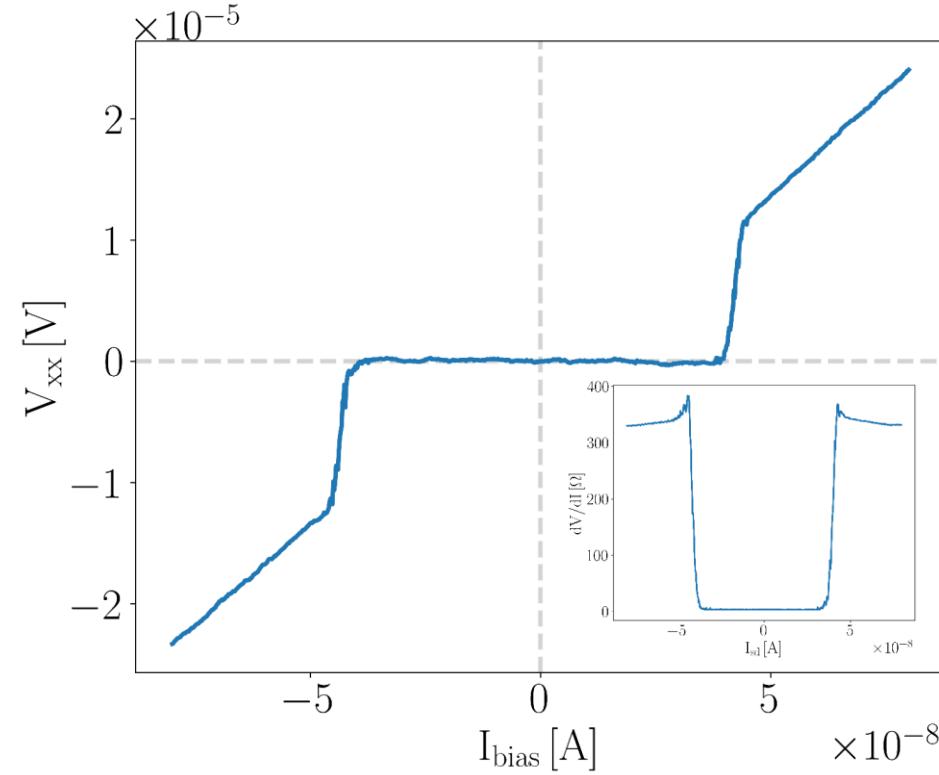
$$\lambda_{\text{mfp}} \sim 500 \text{ nm}$$

InSb nanoflag-based Josephson junctions



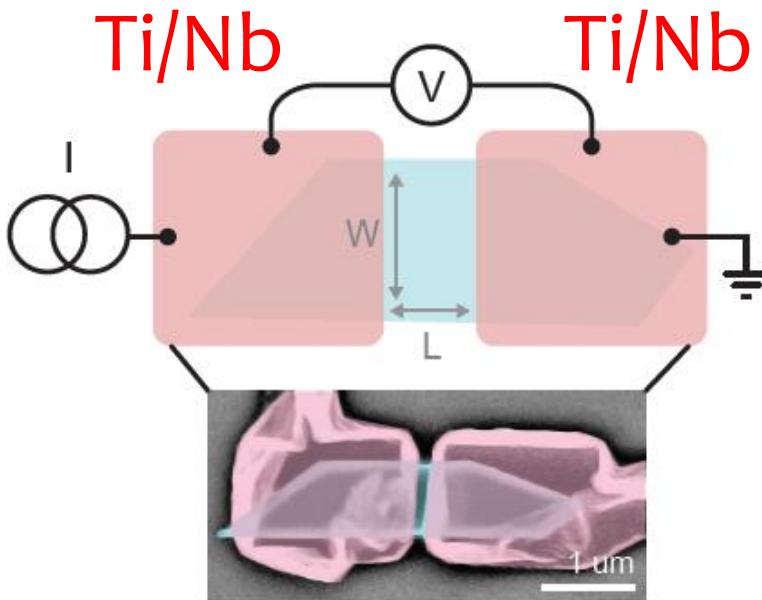
λ_{mfp}	500 nm
L	200 nm
ξ_s	750 nm

short-ballistic junction

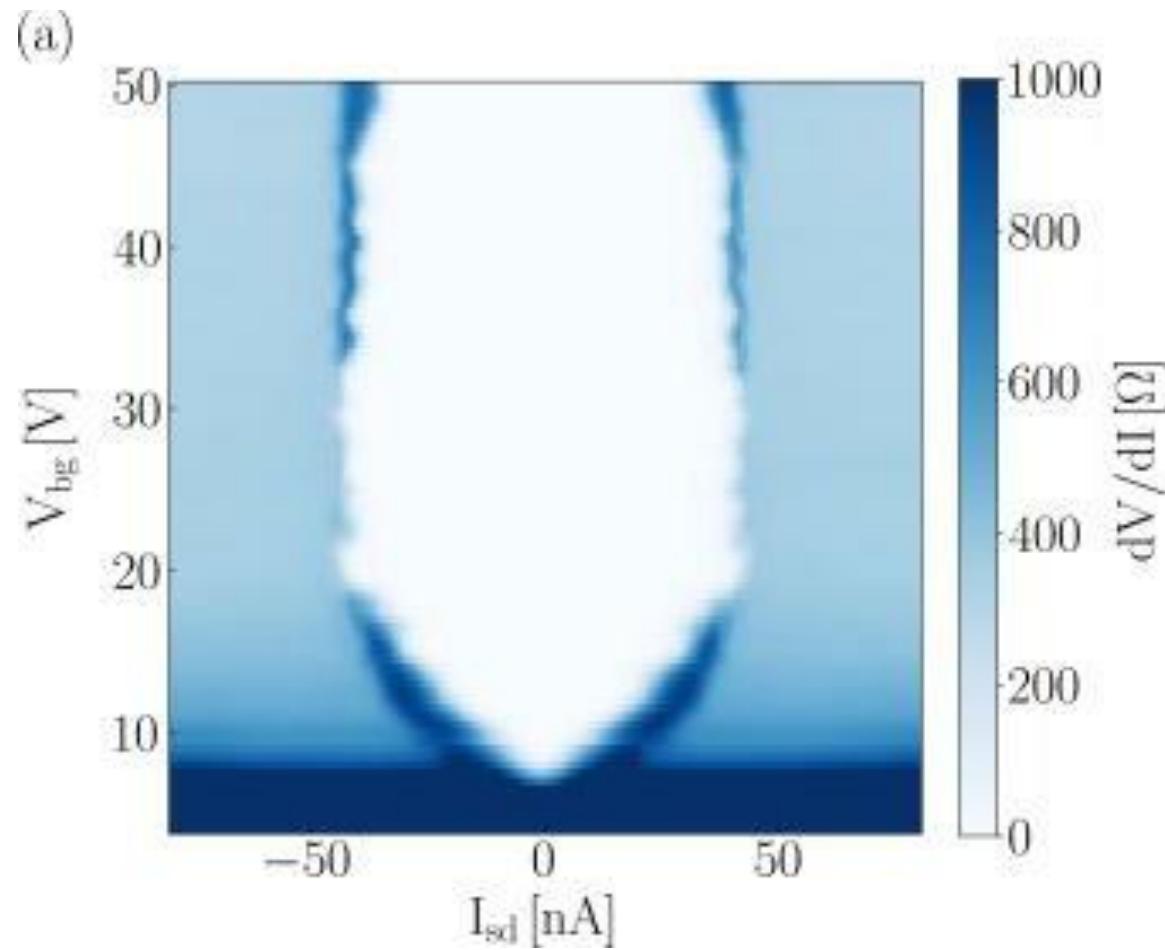


Sedighe Salimian

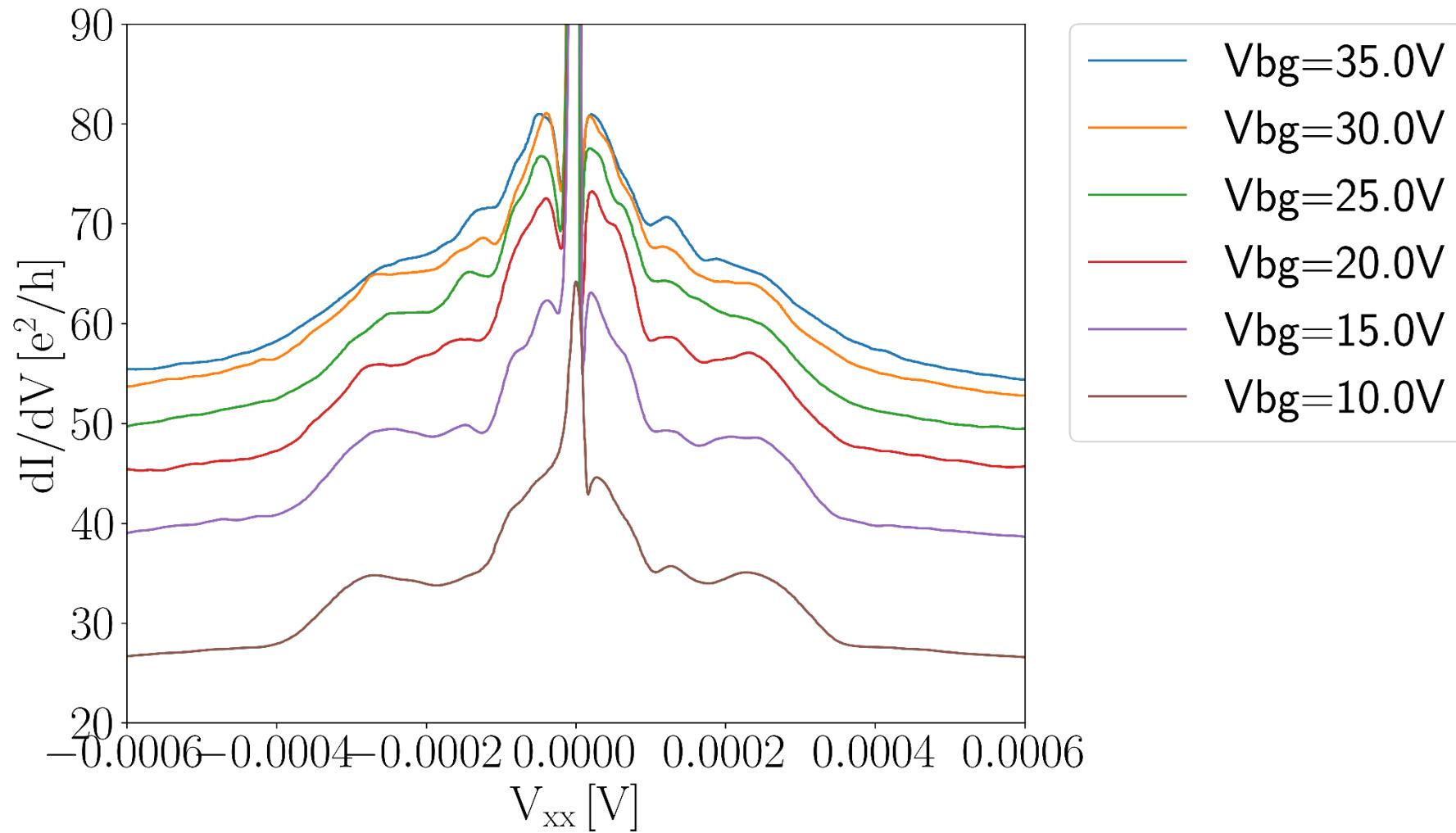
Gate-tunable supercurrent



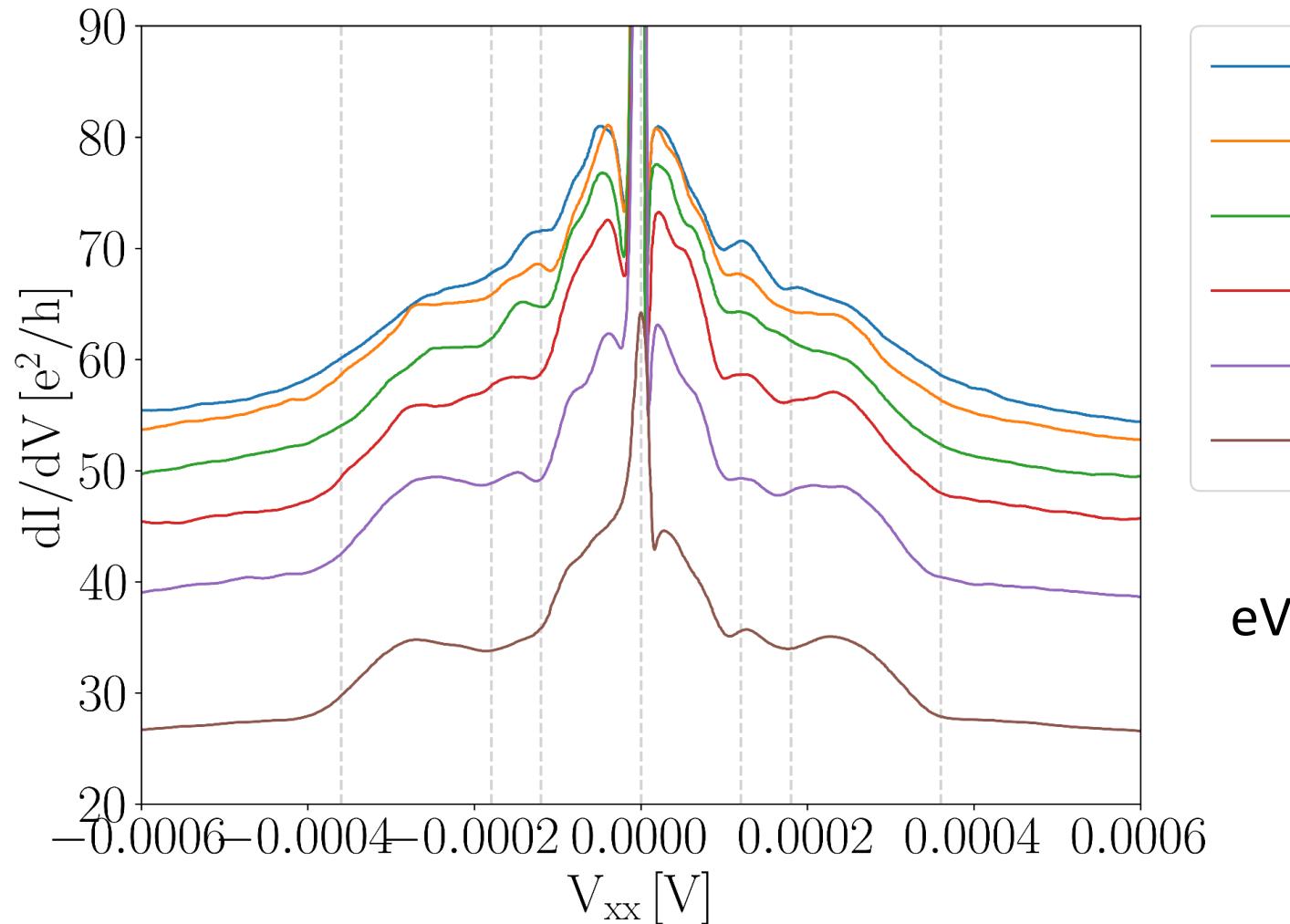
λ_{mfp}	500 nm
L	200 nm
ξ_s	750 nm



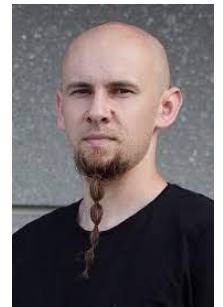
Multiple Andreev Reflections



Multiple Andreev Reflections



- $V_{bg}=35.0\text{V}$
- $V_{bg}=30.0\text{V}$
- $V_{bg}=25.0\text{V}$
- $V_{bg}=20.0\text{V}$
- $V_{bg}=15.0\text{V}$
- $V_{bg}=10.0\text{V}$



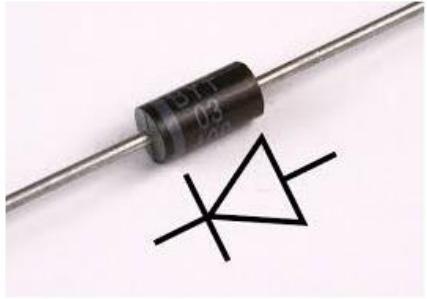
Michał P. Nowak

$$eV(n) = 2\Delta^*/n \quad (n=1, 2, 3 \dots)$$

$$\Delta^* \sim 160 \mu\text{eV}$$

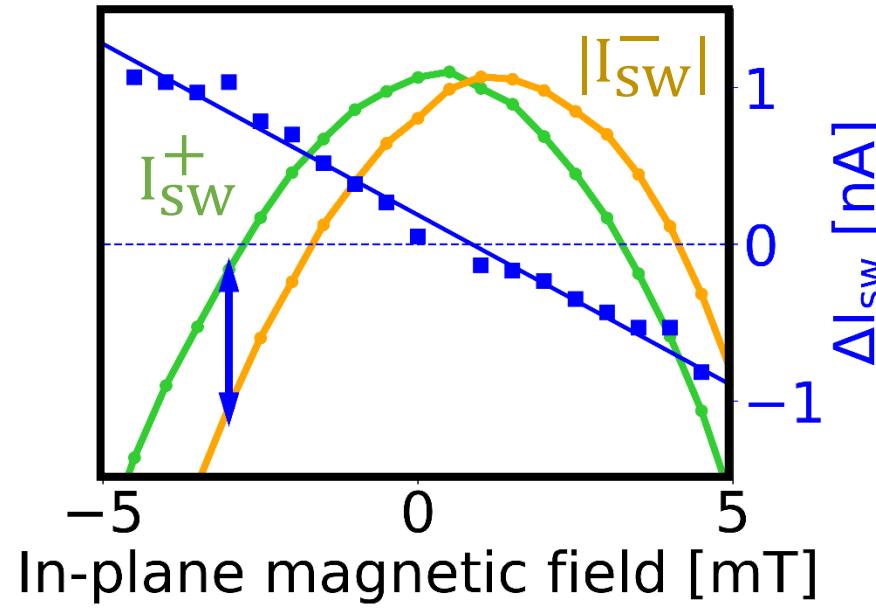
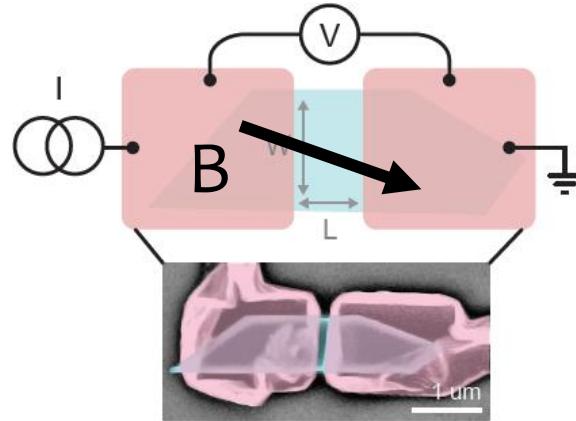
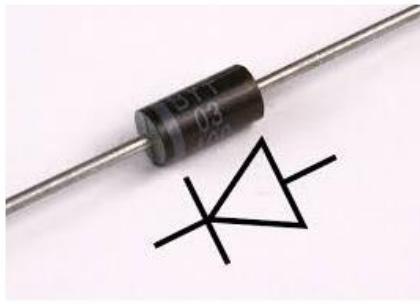
transparency $\tau = 0.94$

Josephson Diode Effect



Bianca Turini

Josephson Diode Effect

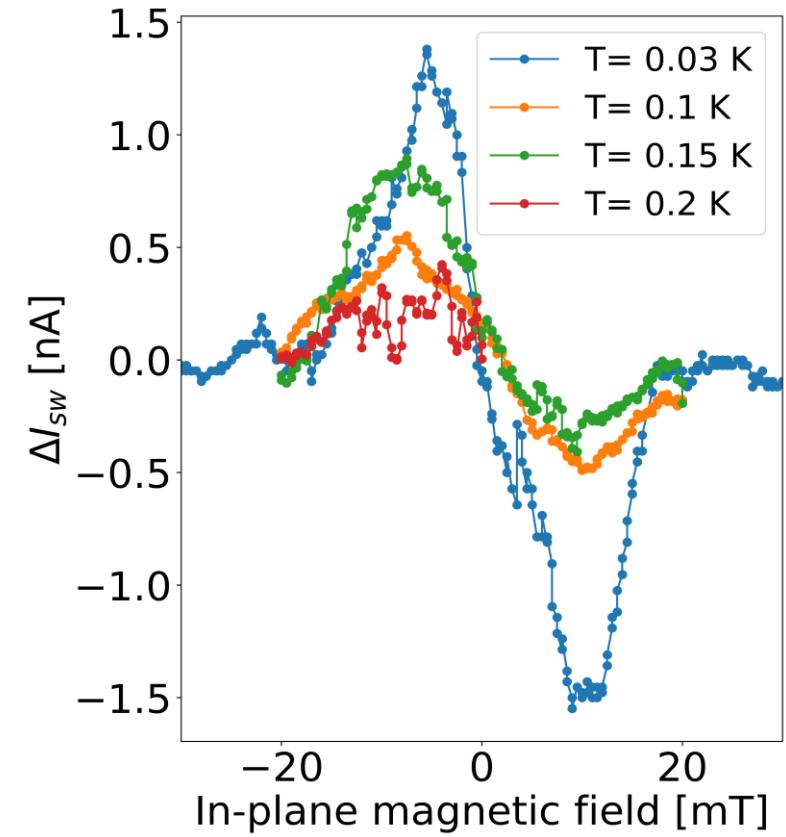
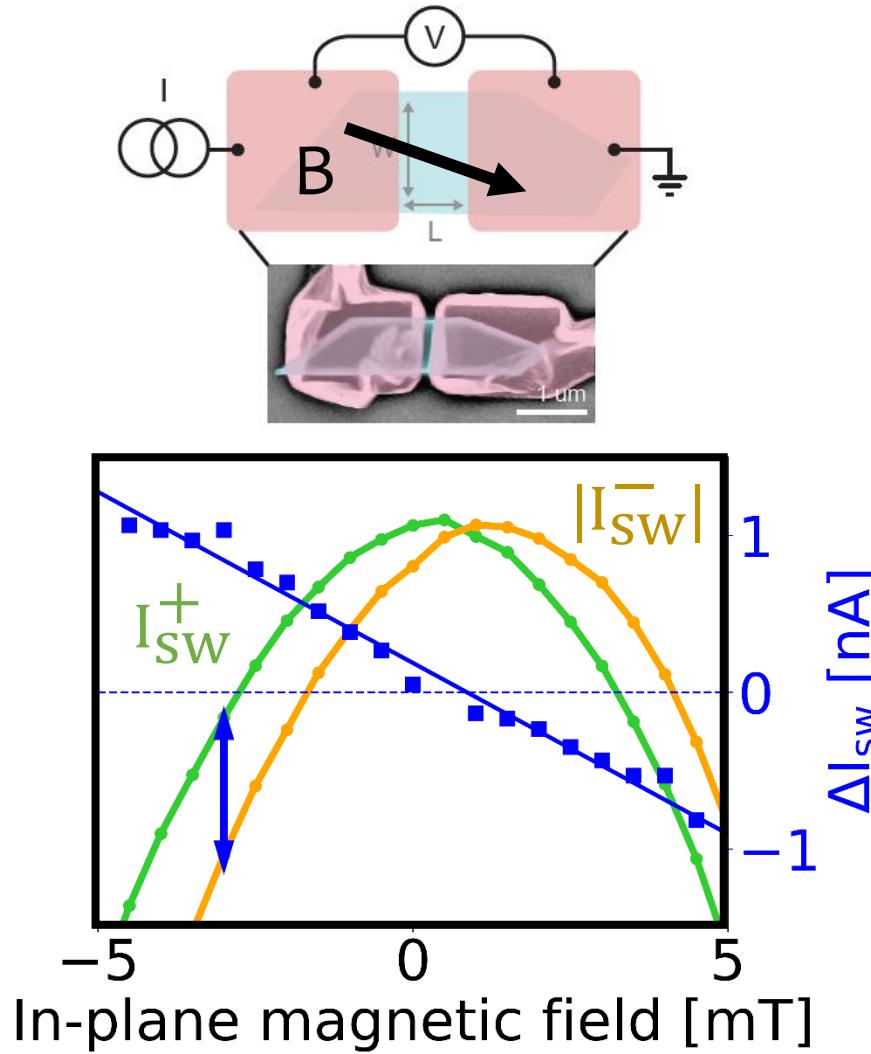
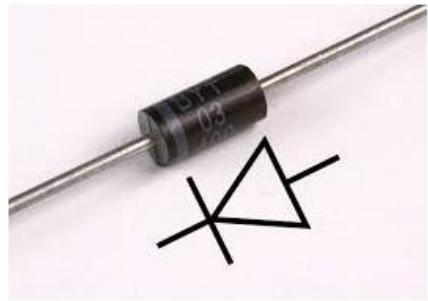


B. Turini et al., Nano Lett. 22, 8502 (2022).

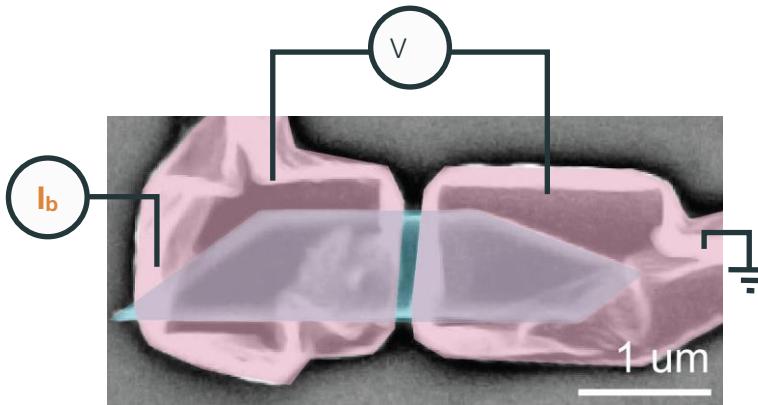


Bianca Turini

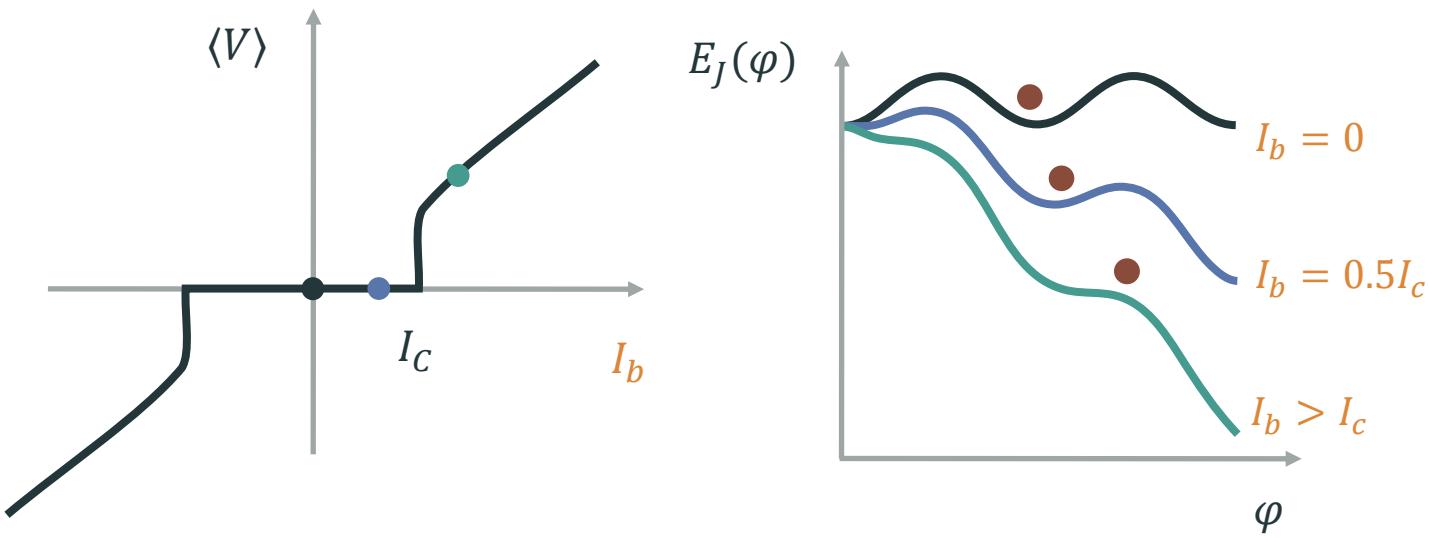
Josephson Diode Effect



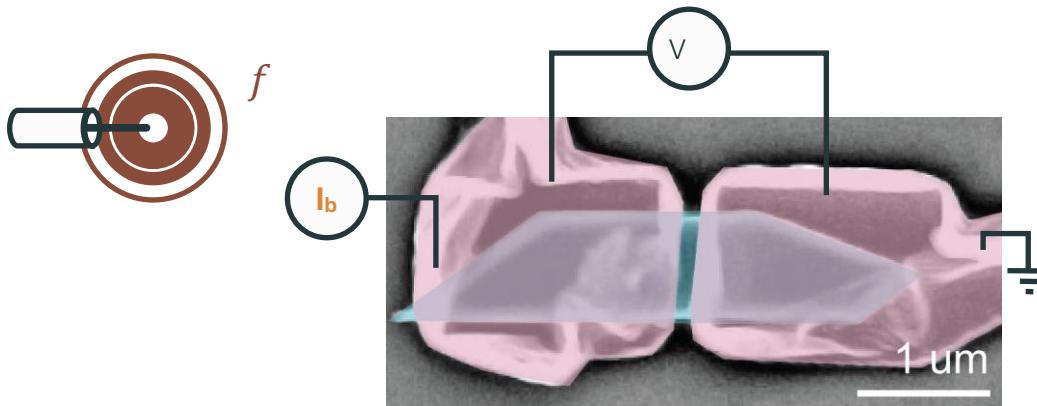
Shapiro steps



$$V = \frac{\hbar}{2e} \dot{\varphi}$$



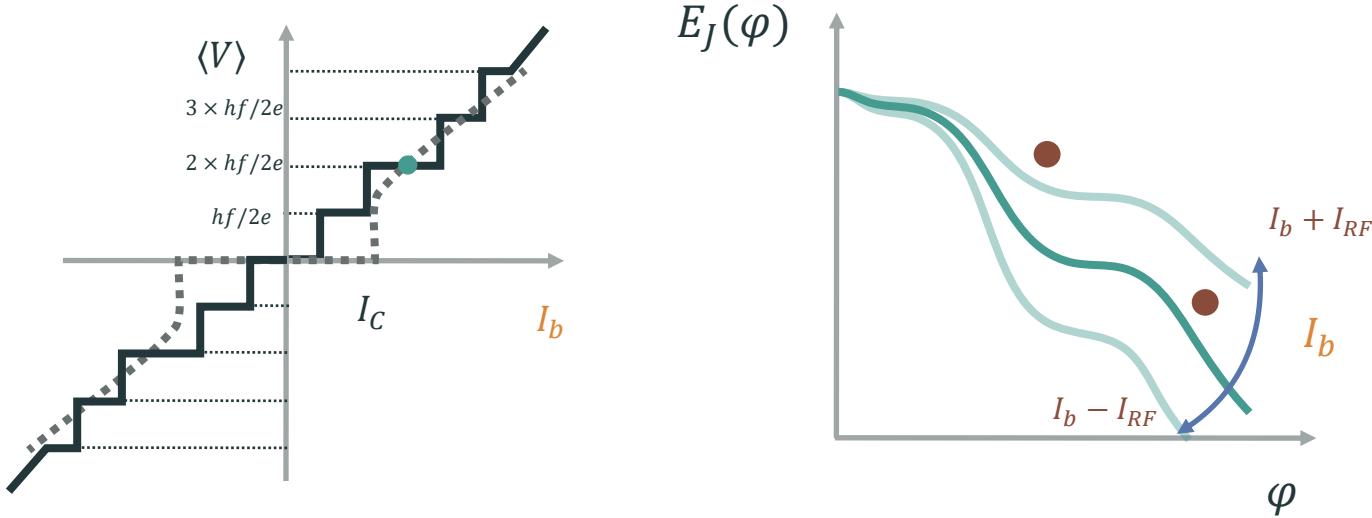
Shapiro steps



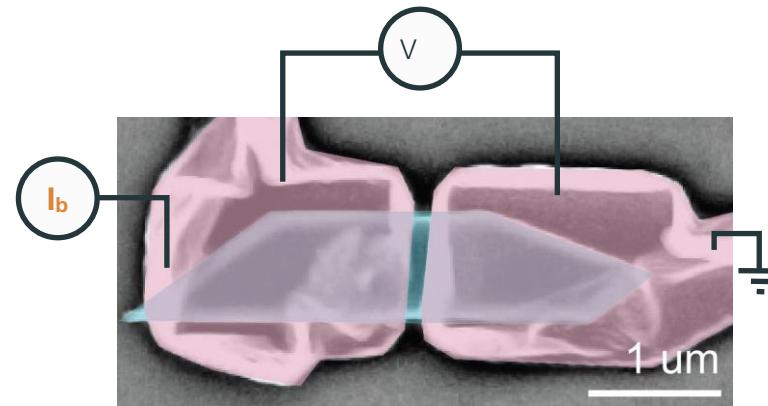
If particle rolls n minima in a period $T = 2\pi/f$, then $\dot{\varphi} = 2\pi n f$

$$V = \frac{\hbar}{2e} \dot{\varphi}$$

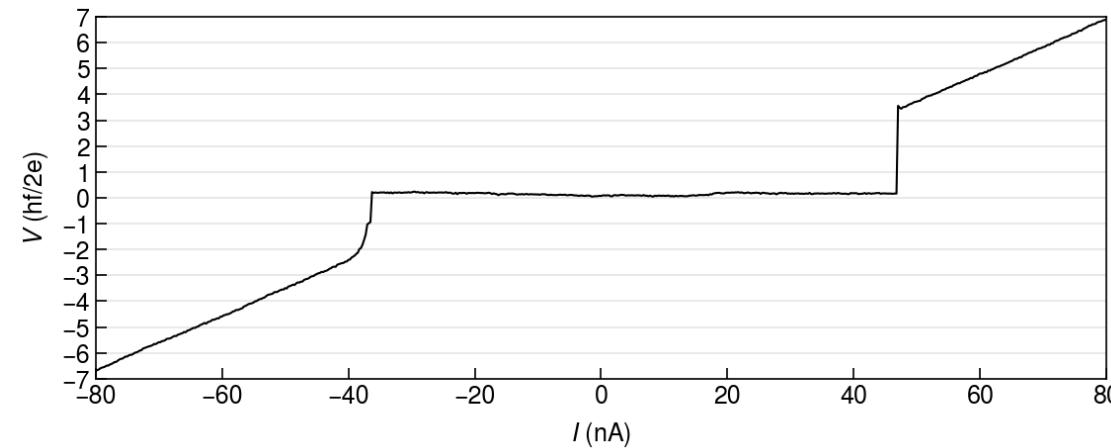
$$= \frac{hf}{2e} n$$



Half-integer Shapiro steps



Andrea Iorio

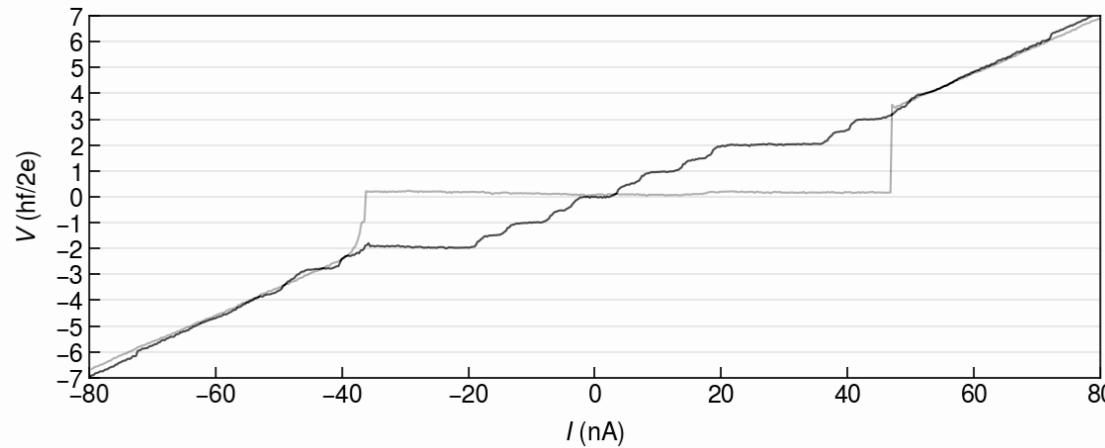
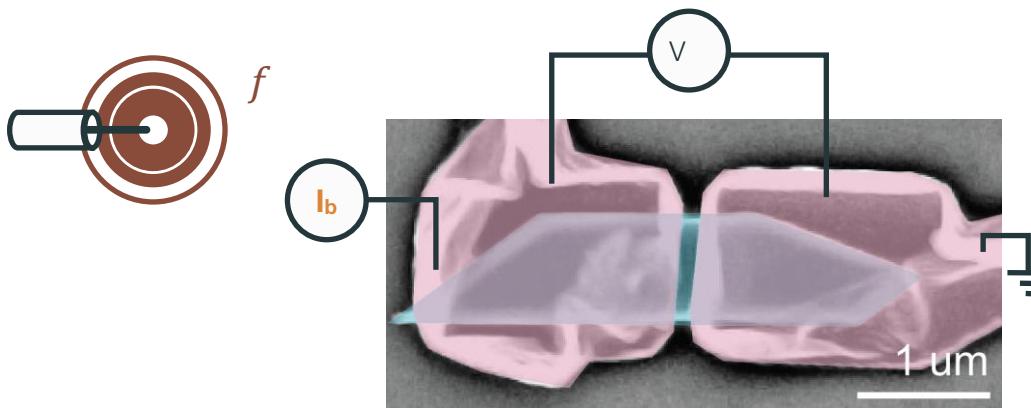


Shapiro steps – Quantized voltage plateaus $V = \frac{hf}{2e} n$

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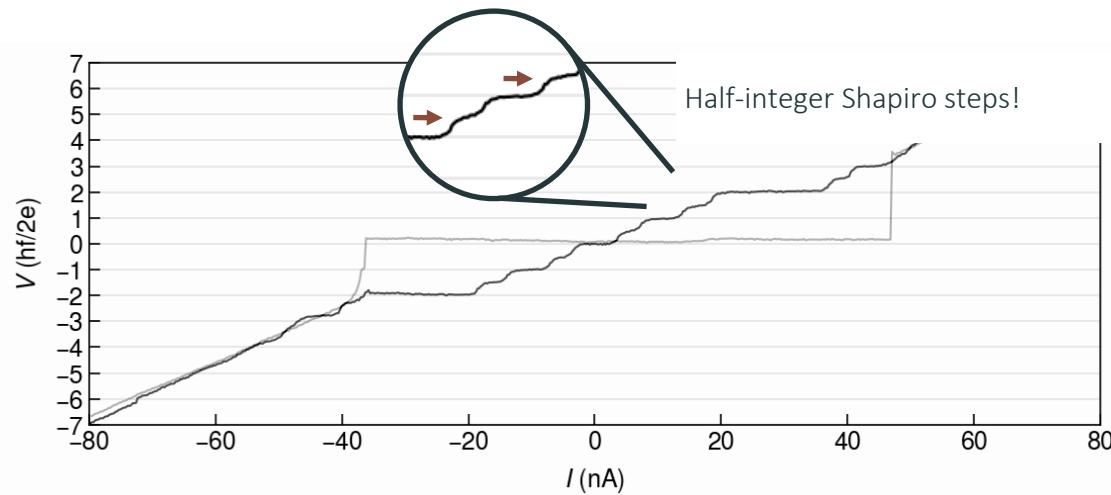
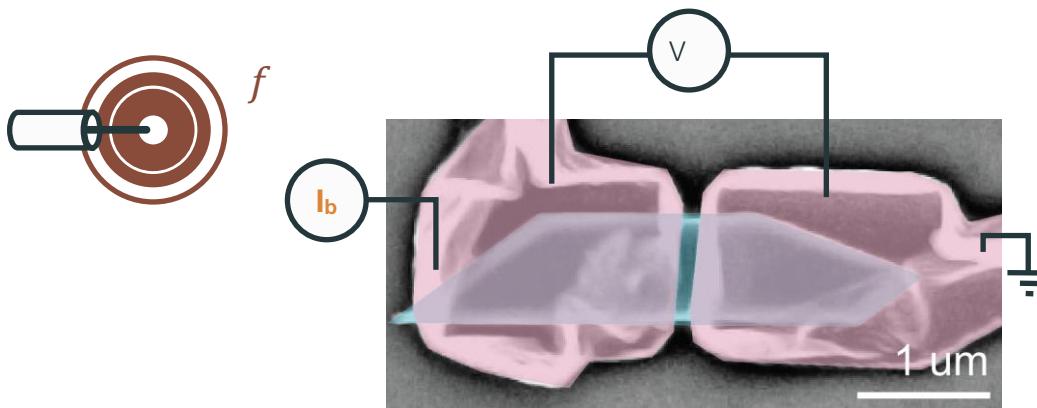
Half-integer Shapiro steps



Shapiro steps – Quantized voltage plateaus $V = \frac{hf}{2e} n$

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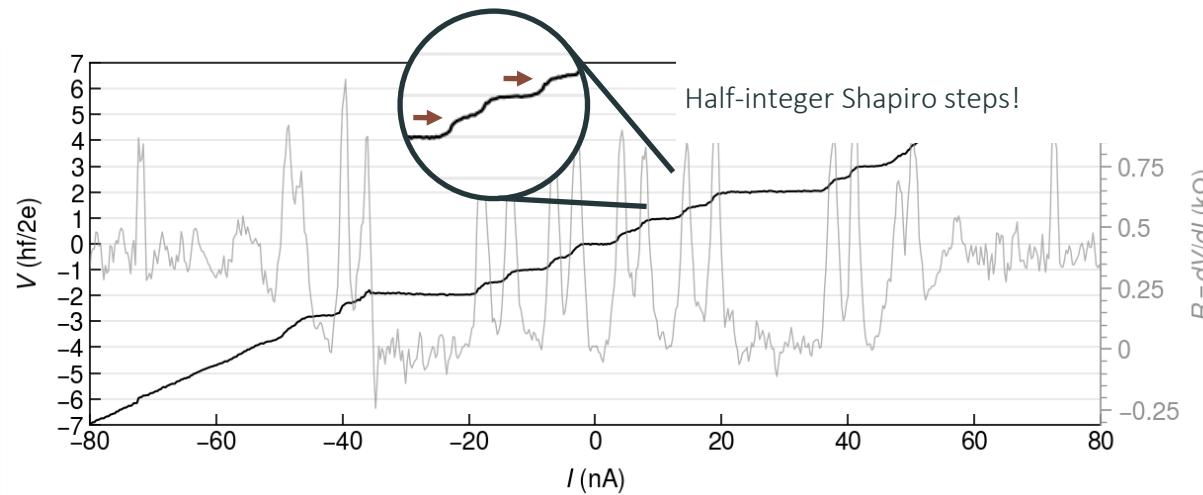
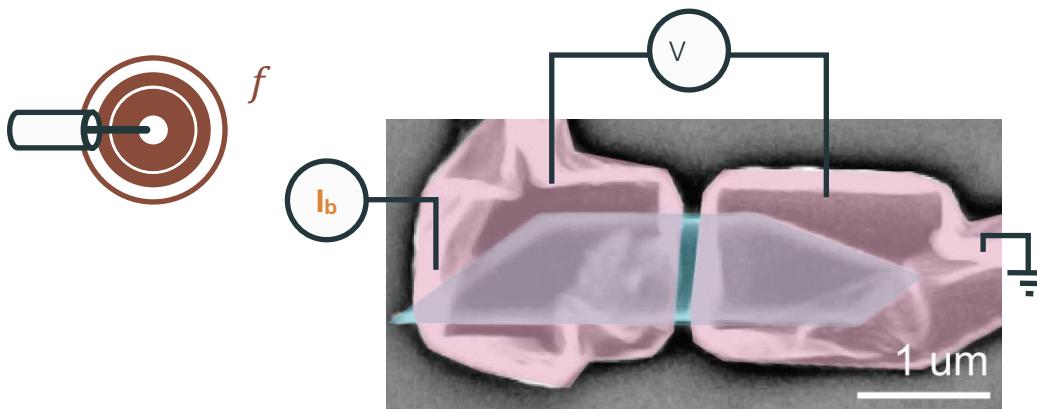
Half-integer Shapiro steps



Shapiro steps – Quantized voltage plateaus $V = \frac{hf}{2e} n$

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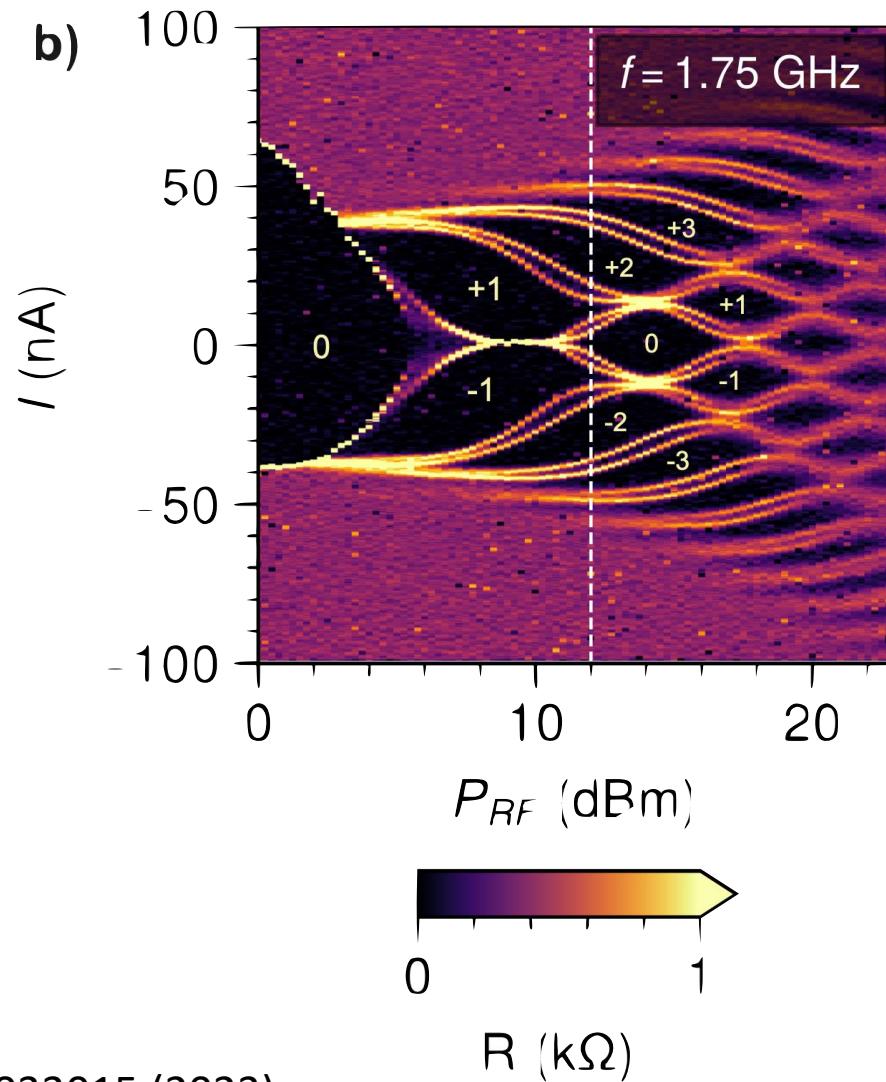
Half-integer Shapiro steps



Shapiro steps – Quantized voltage plateaus $V = \frac{hf}{2e} n$

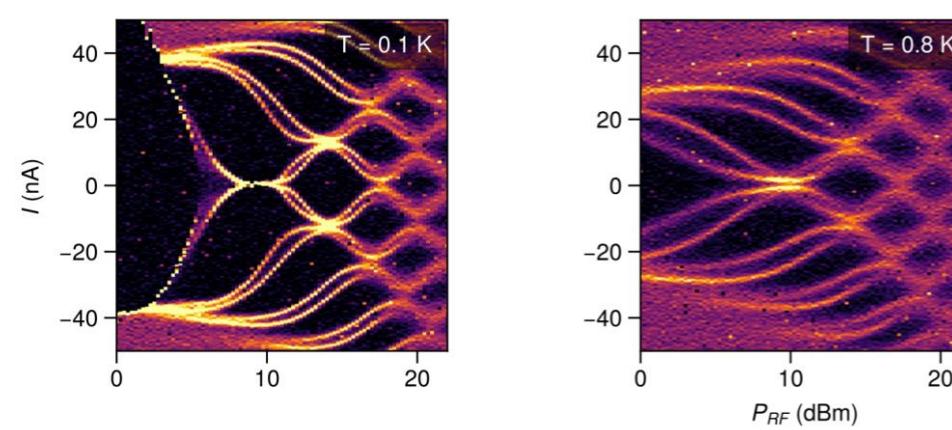
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Half-integer Shapiro steps



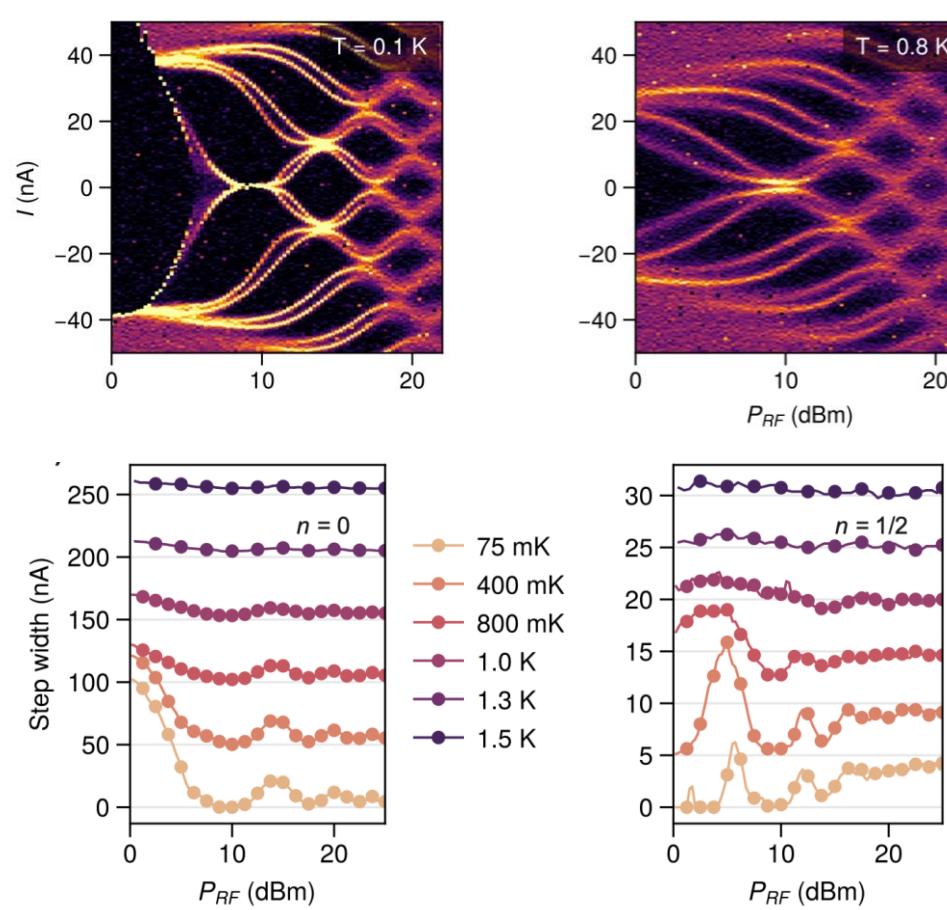
Half-integer Shapiro steps

A non-monotonic temperature dependance



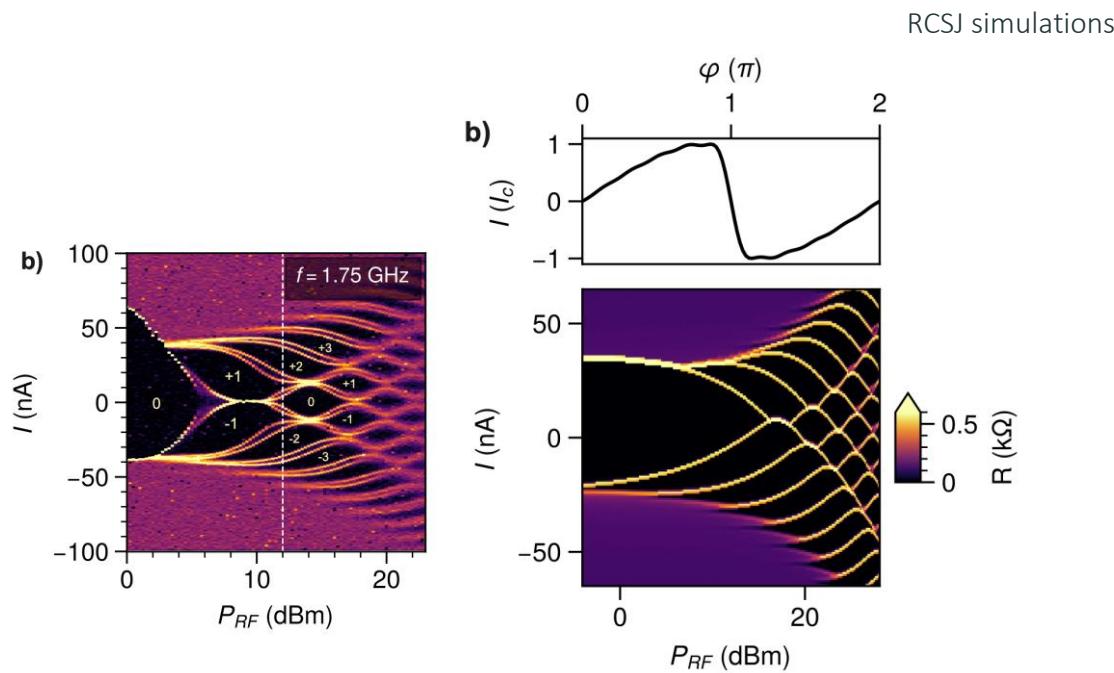
Half-integer Shapiro steps

A non-monotonic temperature dependance



Half-integer Shapiro steps

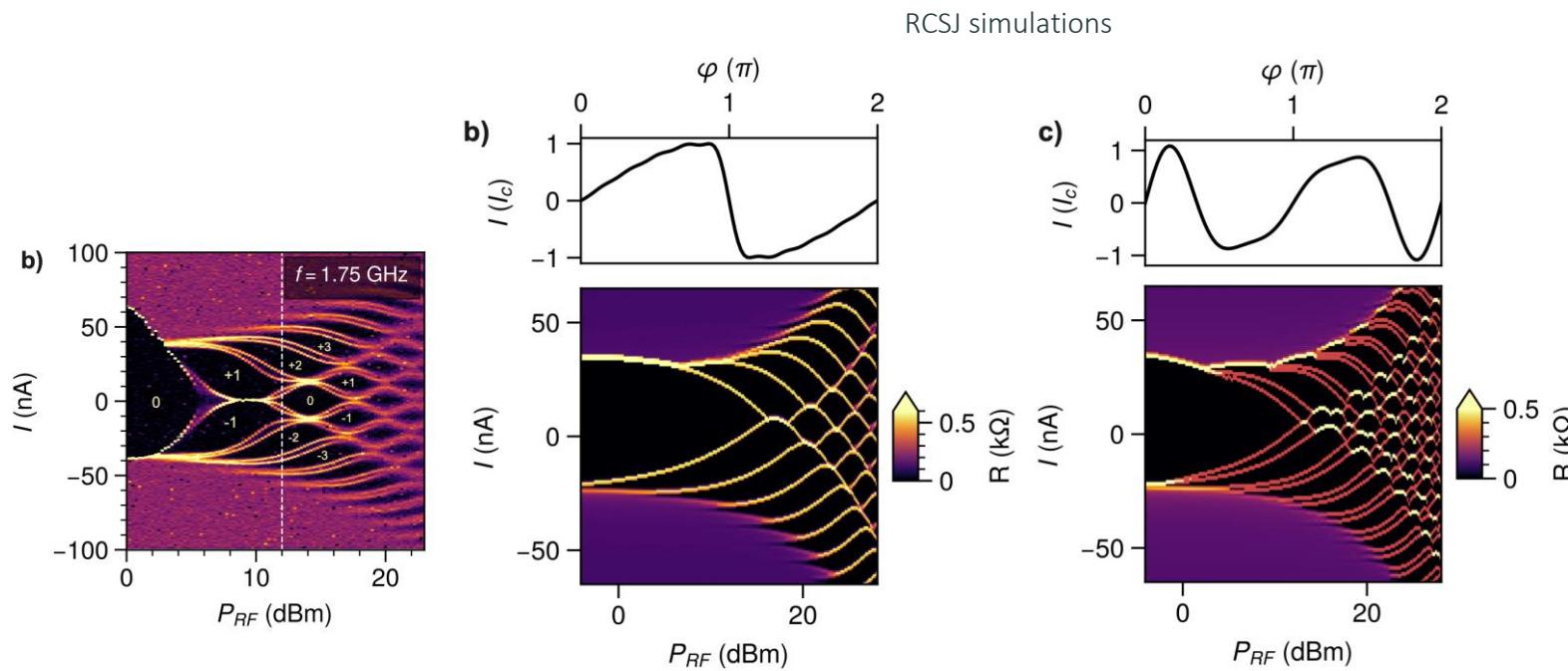
How to have half-integer steps?



Half-integer Shapiro steps

How to have half-integer steps?

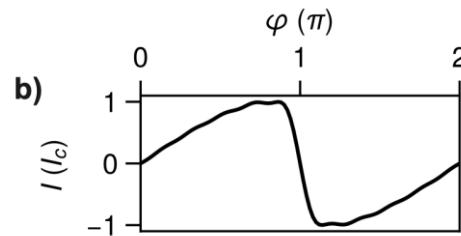
Need for a $\sin(2\varphi)$ CPR



Half-integer Shapiro steps

Potential mechanisms for $\sin(2\varphi)$

Higher harmonic in the equilibrium CPR



✓ Commonly given explanation

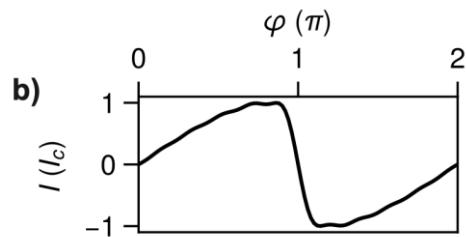
✗ Weaker half-steps

✗ Half-steps decrease with T

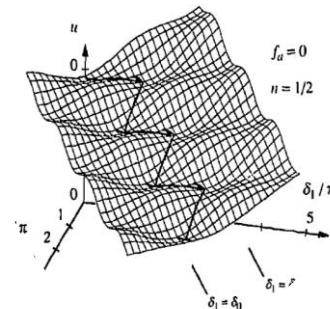
Half-integer Shapiro steps

Potential mechanisms for $\sin(2\varphi)$

Higher harmonic in the equilibrium CPR



SQUID-like



- ✓ Commonly given explanation
- ✓ Robust half-steps
- ✗ Weaker half-steps
- ✗ Different geometry
- ✗ Half-steps decrease with T
- ✗ B-field dependent

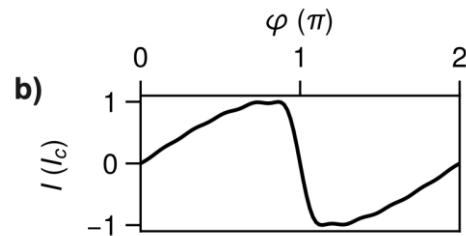
Physical basis for half-integral Shapiro steps in a dc SQUID. Physica C: Superconductivity 245.3-4 (1995)

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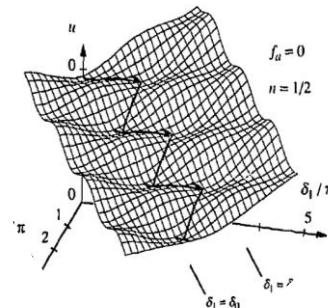
Half-integer Shapiro steps

Potential mechanisms for $\sin(2\varphi)$

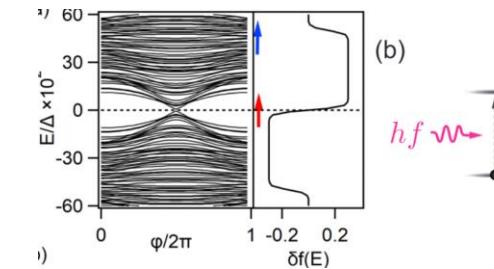
Higher harmonic in the equilibrium CPR



SQUID-like



Non-equilibrium excitations



 Commonly given explanation

 Weaker half-steps

 Half-steps decrease with T

 Robust half-steps

 Different geometry

 B-field dependent

 $\sin(2\varphi)$ only when driving

 Half-steps non-monotonic in T

 Still some gaps with the theory

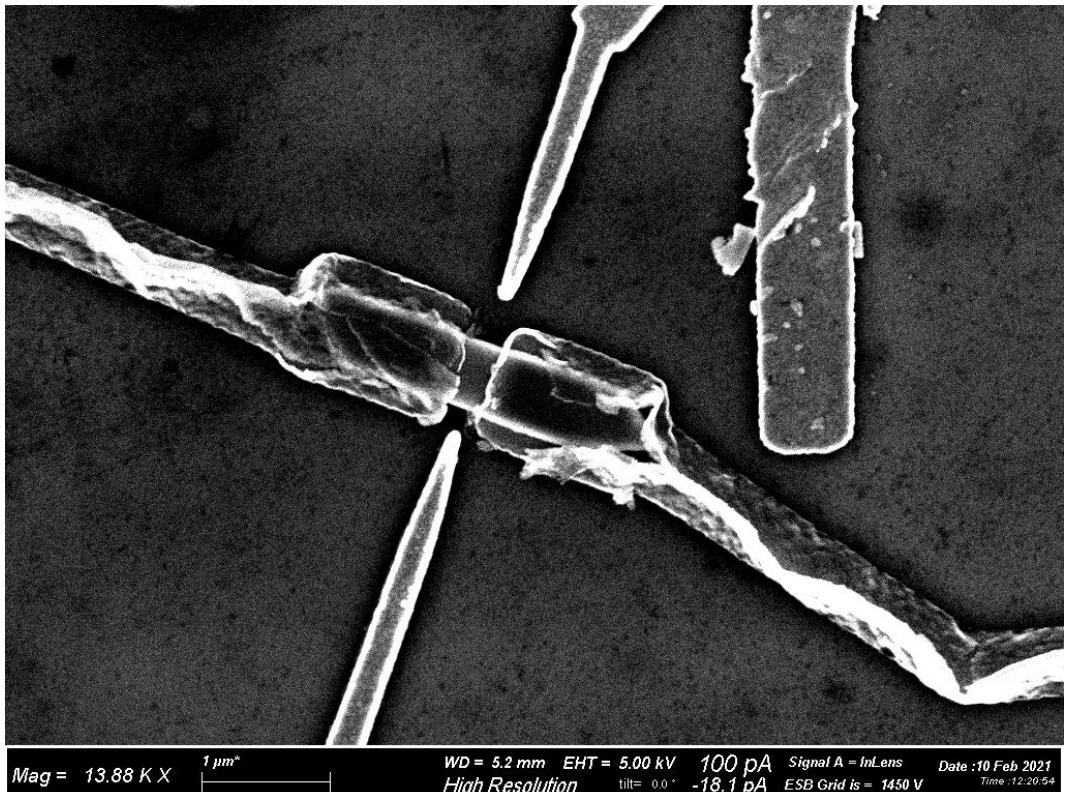
Physical basis for half-integral Shapiro steps in a dc SQUID. Physica C: Superconductivity 245.3-4 (1995)

Theory of microwave-assisted supercurrent in quantum point contacts. Physical review letters 105.11 (2010)
Microwave photoassisted dissipation and supercurrent of a phase-biased graphene-superconductor ring. Physical Review Research 3.3 (2021)

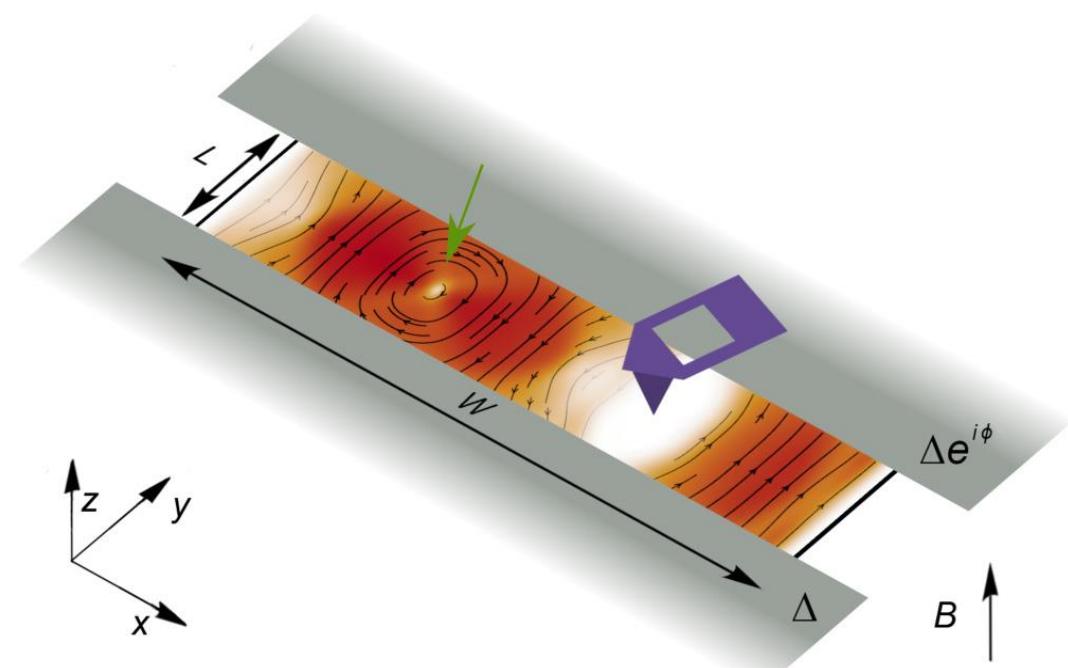
Science and nanoTechnology

Outlook

Gate-controlled JJs



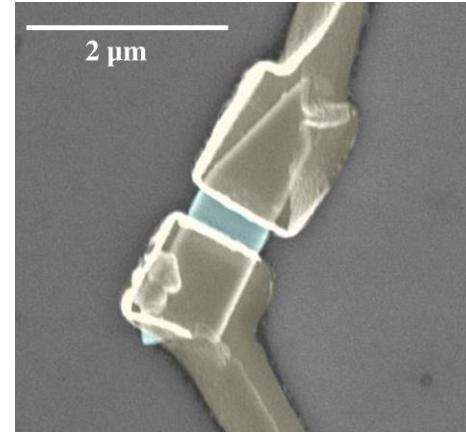
SGM on these JJs



K. Kaperek et al., Phys. Rev. B 106 (2022) 035432
S. Fracassi et al., arXiv:2403.17894
Appl. Phys. Lett. 124 (2024); doi: 10.1063/5.0210660

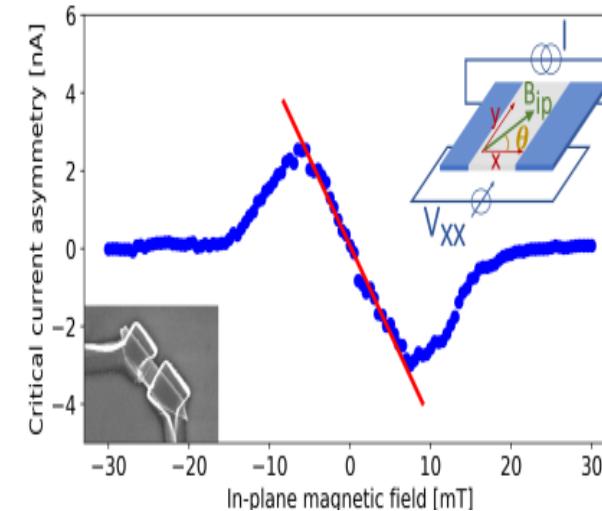
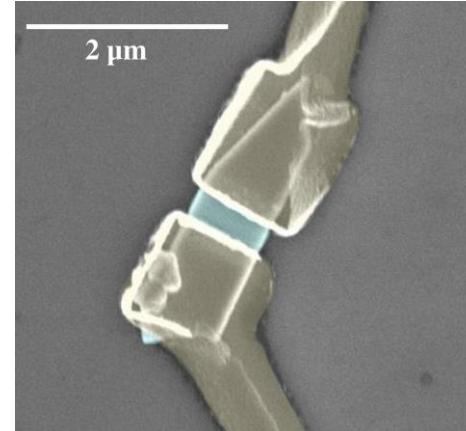
Summary

- InSb nanoflag-based Josephson junctions:
 - High-transparency of the interfaces
 - Ballistic transport
 - Gate-controlled supercurrent
- Josephson diode effect:
 - First observation of the JDE in InSb
 - Magnetic field-driven rectification
 - Relevance of Rashba SOC in the system
- Half-integer Shapiro steps:
 - Shapiro steps are still an open-topic in SNS devices
 - Controllable manipulation of bound states excitations (Andreev qubits)



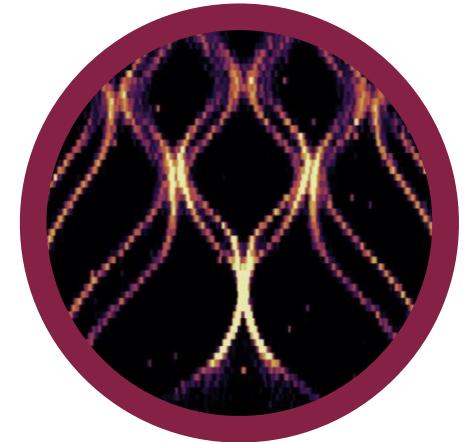
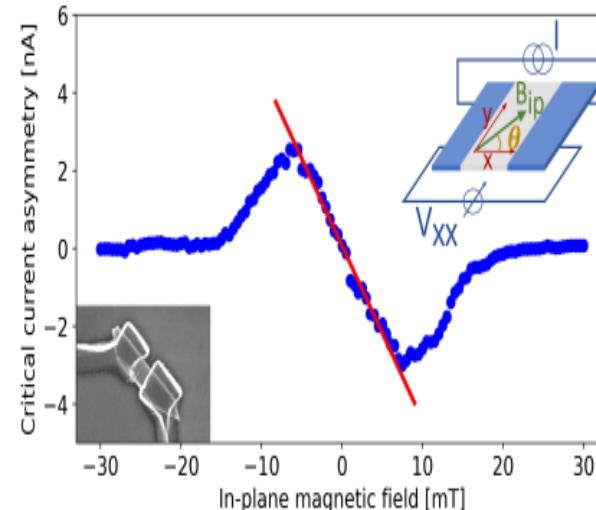
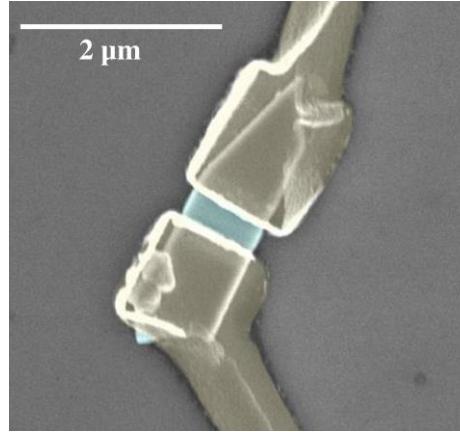
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Thank you for your attention!

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